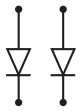
CMFD2004i

SURFACE MOUNT
DUAL ISOLATED HIGH VOLTAGE
SILICON SWITCHING DIODES





SOT-143 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMFD2004i consists of two electrically Isolated high voltage switching diodes packaged in an epoxy molded SOT-143 surface mount case. This device is designed for switching applications requiring dual high voltage diodes.

MARKING CODE: CJP

MAXIMUM RATINGS: (T_A=25°C)	**SYMBOL**		**UNITS**
Continuous Reverse Voltage	V_R	240	V
Peak Repetitive Reverse Voltage	V_{RRM}	300	V
Peak Repetitive Reverse Current	I_O	200	mA
Continuous Forward Current	I_F	225	mA
Peak Repetitive Forward Current	I_{FRM}	450	mA
Peak Forward Surge Current, tp=1.0μs	I_{FSM}	4.0	A
Peak Forward Surge Current, tp=1.0s	I_{FSM}	1.0	A
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

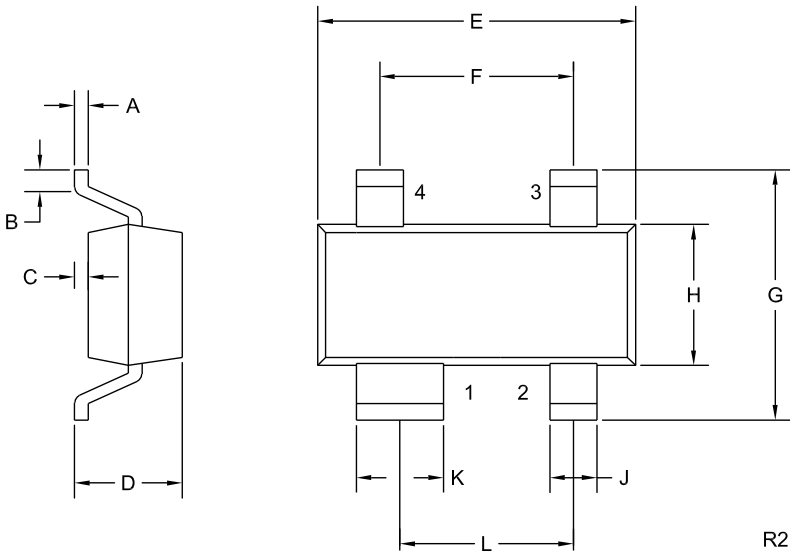
SYMBOL	**TEST CONDITIONS**	**MIN**	**MAX**	**UNITS**
I_R	V_R=240V		100	nA
I_R	V_R=240V, T_A=150°C		100	μA
BV_R	I_R=100μA	300		V
V_F	I_F=100mA		1.0	V
C_T	V_R=0, f=1.0MHz		5.0	pF
t_{rr}	I_F=I_R=30mA, I_{rr}=3.0mA, R_L=100Ω		50	ns

R5 (13-August 2010)

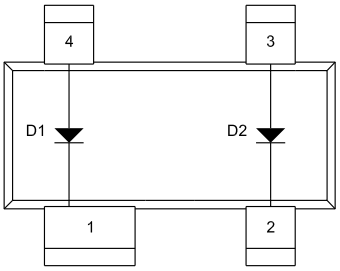
CMFD2004i

SURFACE MOUNT
DUAL ISOLATED HIGH VOLTAGE
SILICON SWITCHING DIODES

SOT-143 CASE - MECHANICAL OUTLINE



PIN CONIGURATION



LEAD CODE:
1) Cathode D1
2) Cathode D2
3) Anode D2
4) Anode D1

MARKING CODE: CJP

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.003	0.006	0.08	0.15
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	-	0.045	-	1.14
E	0.110	0.120	2.79	3.04
F	0.075		1.90	
G	-	0.098	-	2.50
H	0.047	0.055	1.19	1.40
J	0.014	0.020	0.36	0.50
K	0.030	0.037	0.76	0.93
L	0.067		1.70	

SOT-143 (REV: R2)